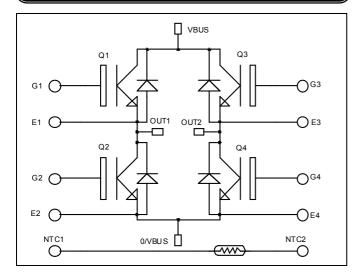


Full - Bridge Fast Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 1200V$$

 $I_C = 50A$ @ $Tc = 80$ °C

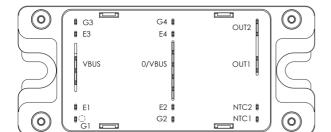


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	75	
I _C	Continuous Collector Current	$T_C = 80$ °C	50	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	277	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	100A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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www.microsemi.com



All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.7	2.1	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 50A$ $T_j = 125$	$T_j = 125$ °C		2.0		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 2mA$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			3600		
C_{oes}	Output Capacitance				190		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		160			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ing (25°C)		90		
$T_{\rm r}$	Rise Time	$V_{GE} = 15V$			30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 50A$			420		ns
T_{f}	Fall Time	$R_G = 18 \Omega$		70			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ing (125°C)		90		
T_{r}	Rise Time	$V_{GE} = 15V$			50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 50A$			520		ns
T_{f}	Fall Time	$R_G = 18 \Omega$			90		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		5		T
E_{off}	Turn-off Switching Energy	$I_C = 50A$ $R_G = 18 \Omega$	$T_j = 125$ °C		5.5		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Payaraa Laakaaa Cumunt	V _R =1200V	$T_j = 25$ °C			250	^
1 _{RM}	Maximum Reverse Leakage Current	V _R -1200 V	$T_j = 125$ °C			500	μA
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		50		A
V_{F}	Diode Forward Voltage	$I_F = 50A$	$T_i = 25^{\circ}C$		1.4	1.9	V
* F			$T_{i} = 125^{\circ}C$		1.3		_ '
t _{rr}	Reverse Recovery Time		$T_j = 25$ °C		150		ns
чт	reverse receivery Time		$T_{j} = 125^{\circ}C$		250		115
Q_{rr}	Reverse Recovery Charge	$ \begin{aligned} I_F &= 50A \\ V_R &= 600V \\ di/dt &= 2000A/\mu s \end{aligned} $	$T_j = 25^{\circ}C$		4.5		μС
Qrr	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		9		μС
E _r	Reverse Recovery Energy		$T_j = 25$ °C		2.1		mJ
\mathbf{L}_{r}			$T_j = 125$ °C		4.2		1117

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Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

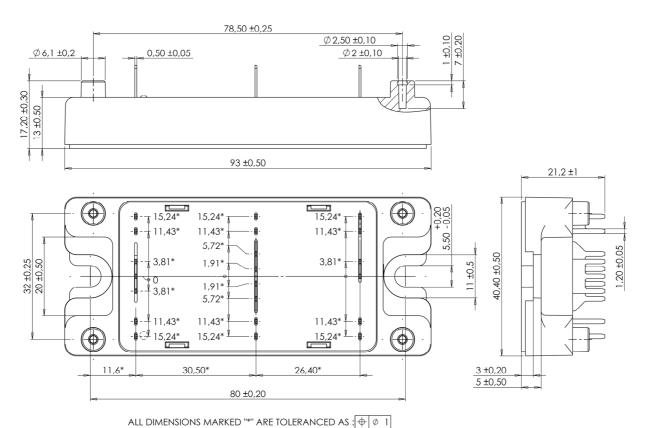
$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{75}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance IGBT Diode		IGBT			0.45	°C/W
			Diode			0.58	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range		-40		150		
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

SP4 Package outline (dimensions in mm)

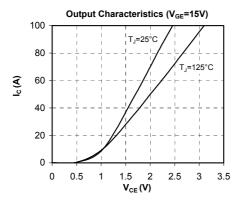


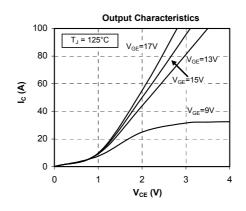
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

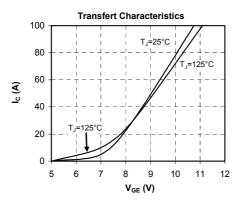
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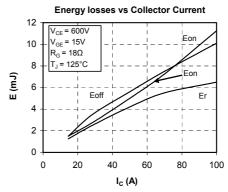


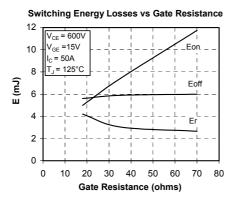
Typical Performance Curve

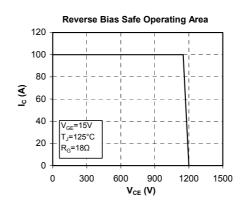


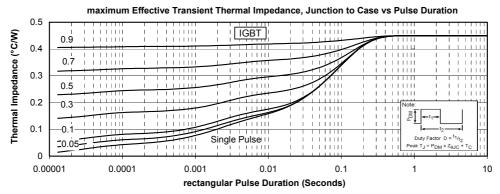






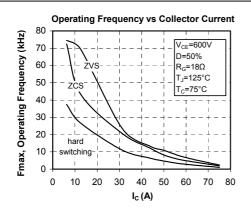


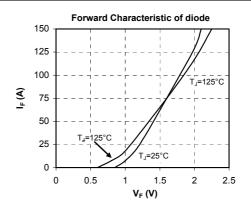


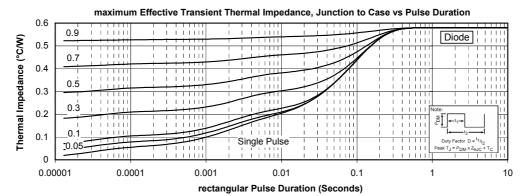


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